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(56) **References Cited**

U.S. PATENT DOCUMENTS

2008/0224233 A1	9/2008	Masliah	
2009/0256199 A1*	10/2009	Denison H01L 29/0653 257/343
2010/0140715 A1*	6/2010	Nakamura H01L 29/0653 257/368
2010/0163987 A1	7/2010	Nakagawa	
2011/0193167 A1*	8/2011	Fung H01L 21/26506 257/350
2012/0043608 A1*	2/2012	Yang et al. 257/336

FOREIGN PATENT DOCUMENTS

JP	2010157688 A	7/2010
WO	2010046794 A1	4/2010

OTHER PUBLICATIONS

Sonsky J., et al., "Innovative High Voltage transistors for complex HV/RF SoCs in baseline CMOS", VLSI Technology, Systems and Applications, 2008. VLSI-TSA 2008. International Symposium on, IEEE, Piscataway, NJ, USA, Apr. 21, 2008, pp. 115-116, XP031258840, ISBN: 978-1-4244-1614-1 the whole document.

Udrea F, "SOI-based Devices and Technologies for High Voltage ICs", Bipolar/BiCMOS Circuits and Technology Meeting, 2007. BCTM '07. IEEE, Sep. 30, 2007, pp. 74-81.

Perez-Gonzalez J., et al., "HCl Reliability Control in HV-PMOS Transistors: Conventional EDMOS vs Dielectric Resurf and Lateral Field Plates", 21st International Symposium on Power Semiconductor Devices & IC's, IEEE, IEDM, Jun. 2009, pp. 61-64.

* cited by examiner